FAIRCHILD SEMICONDUCTOR®

September 2001

FDFS2P103

Integrated P-Channel PowerTrench® MOSFET and Schottky Diode

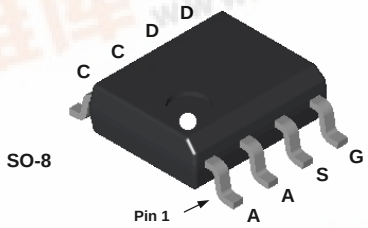
General Description

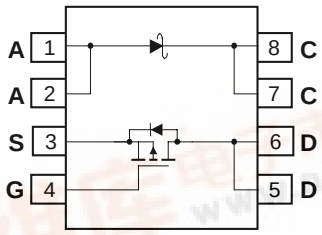
The FDFS2P103 combines the exceptional performance of Fairchild's PowerTrench MOSFET technology with a very low forward voltage drop Schottky barrier rectifier in an SO-8 package.

This device is designed specifically as a single package solution for DC to DC converters. It features a fast switching, low gate charge MOSFET with very low on-state resistance. The independently connected Schottky diode allows its use in a variety of DC/DC converter topologies.

Features

- –5.3 A, –30V $R_{DS(ON)}$ = 59 mΩ @ V_{GS} = –10 V
  $R_{DS(ON)}$ = 92 mΩ @ V_{GS} = –4.5 V
- V_F < 0.52 V @ 1 A (T_J = 125°C)
  V_F < 0.57 V @ 1 A (T_J = 25°C)
- Schottky and MOSFET incorporated into single power surface mount SO-8 package
- Electrically independent Schottky and MOSFET pinout for design flexibility





Absolute Maximum Ratings

T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	MOSFET Drain-Source Voltage		–30	V
V_{GSS}	MOSFET Gate-Source Voltage		±25	V
I_D	Drain Current – Continuous	(Note 1a)	–5.3	A
	– Pulsed		–20	
P_D	Power Dissipation for Dual Operation		2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C
V_{RRM}	Schottky Repetitive Peak Reverse Voltage		30	V
I_O	Schottky Average Forward Current	(Note 1a)	1	A

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDFS2P103	FDFS2P103	13”	12mm	2500 units

Electrical Characteristics

T_A = 25°C unless otherwise noted

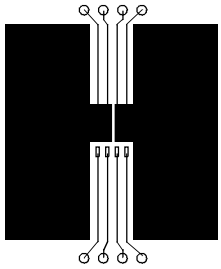
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = –250 μA	–30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = –250 μA,Referenced to 25°C		–23		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = –24 V, V_{GS} = 0 V			–1	μA
I_{GSSF}	Gate–Body Leakage, Forward	V_{GS} = 25 V, V_{DS} = 0 V			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	V_{GS} = –25 V, V_{DS} = 0 V			–100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = –250 μA	–1	–1.7	–3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = –250 μA,Referenced to 25°C		4.5		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = –10 V, I_D = –5.3 A V_{GS} = –4.5 V, I_D = –4 A V_{GS}=–10 V, I_D =–5.3A, T_J=125°C		46 70 63	59 92 88	mΩ
$I_{D(on)}$	On–State Drain Current	V_{GS} = –10 V, V_{DS} = –5 V	–20			A
g_{FS}	Forward Transconductance	V_{DS} = –5V, I_D = –5.3 A		10		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = –15 V, V_{GS} = 0 V, f = 1.0 MHz		528		pF
C_{oss}	Output Capacitance			132		pF
C_{rss}	Reverse Transfer Capacitance			70		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = –15 V, I_D = –1 A, V_{GS} = –10 V, R_{GEN} = 6 Ω		7	14	ns
t_r	Turn–On Rise Time			13	24	ns
$t_{d(off)}$	Turn–Off Delay Time			14	25	ns
t_f	Turn–Off Fall Time			9	17	ns
Q_g	Total Gate Charge	V_{DS} = –15 V, I_D = –5.3 A, V_{GS} = –5 V		5.3	8	nC
Q_{gs}	Gate–Source Charge			2.2		nC
Q_{gd}	Gate–Drain Charge			1.6		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				–1.3	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = –1.3 A (Note 2)		–0.7	–1.2	V
Schottky Diode Characteristics						
I_R	Reverse Leakage	V_R = 30 V, T_J = 25°C		15	100	μA
		V_R = 30 V, T_J = 125°C		6	30	mA
V_F	Forward Voltage	I_F = 1A, T_J = 25°C		0.41	0.57	V
		I_F = 1A, T_J = 125°C		0.32	0.52	V

Thermal Characteristics

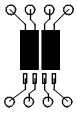
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1c)	135	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Notes:

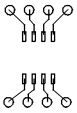
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°C/W when mounted on a $0.5in^2$ pad of 2 oz copper



b) 125°C/W when mounted on a $0.02\ in^2$ pad of 2 oz copper



c) 135°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

Typical Characteristics

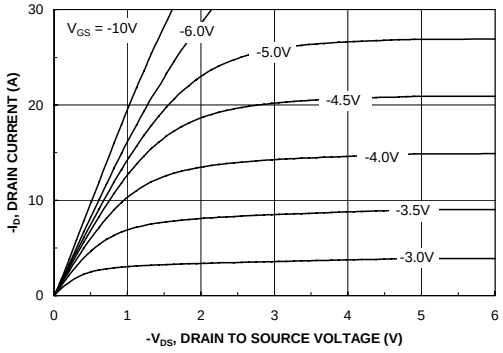


Figure 1. On-Region Characteristics.

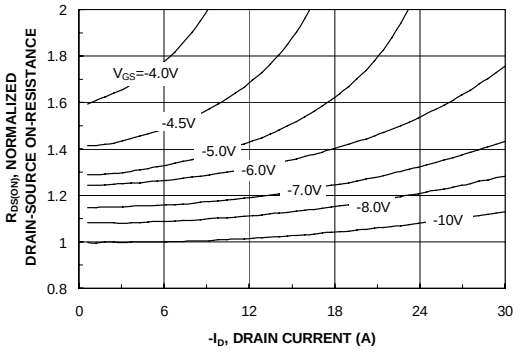


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

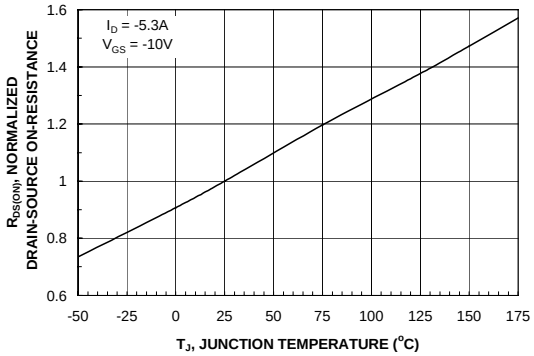


Figure 3. On-Resistance Variation with Temperature.

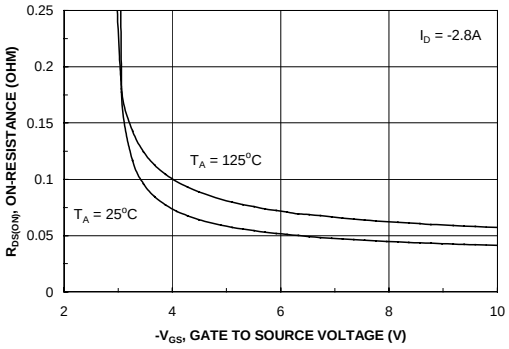


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

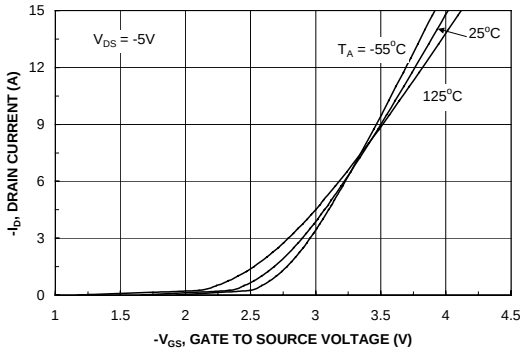


Figure 5. Transfer Characteristics.

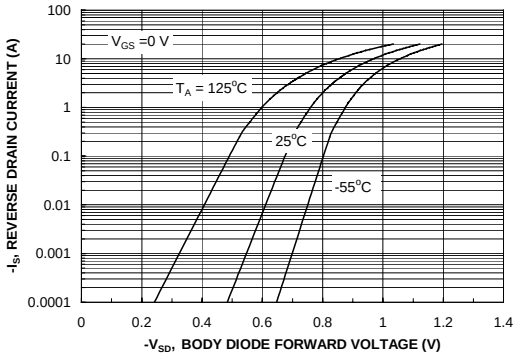


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

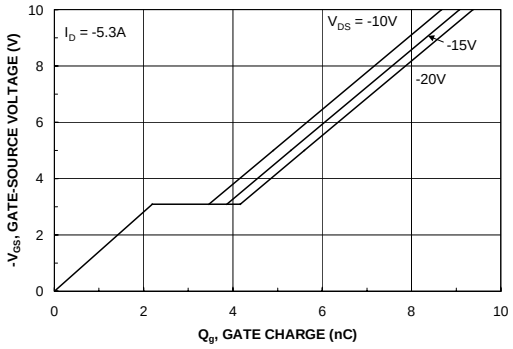


Figure 7. Gate Charge Characteristics.

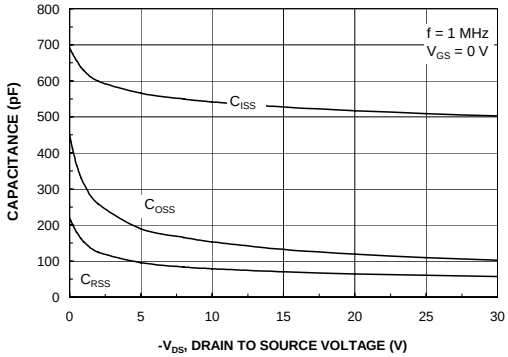


Figure 8. Capacitance Characteristics.

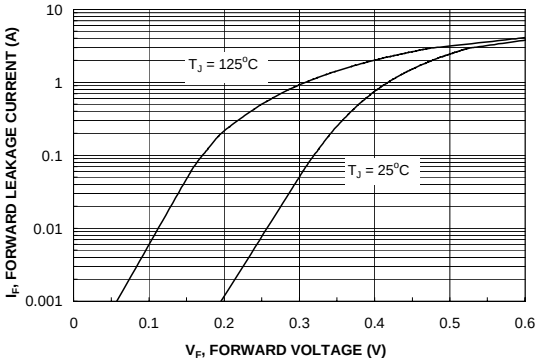


Figure 9. Schottky Diode Forward Voltage.

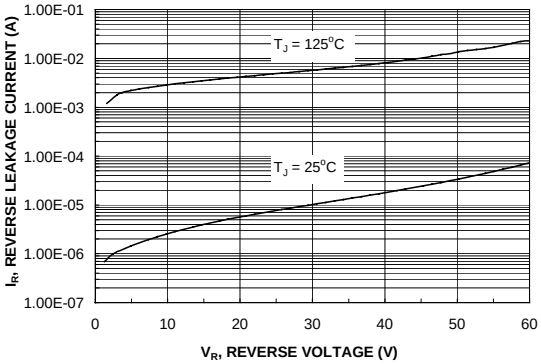


Figure 10. Schottky Diode Reverse Current.

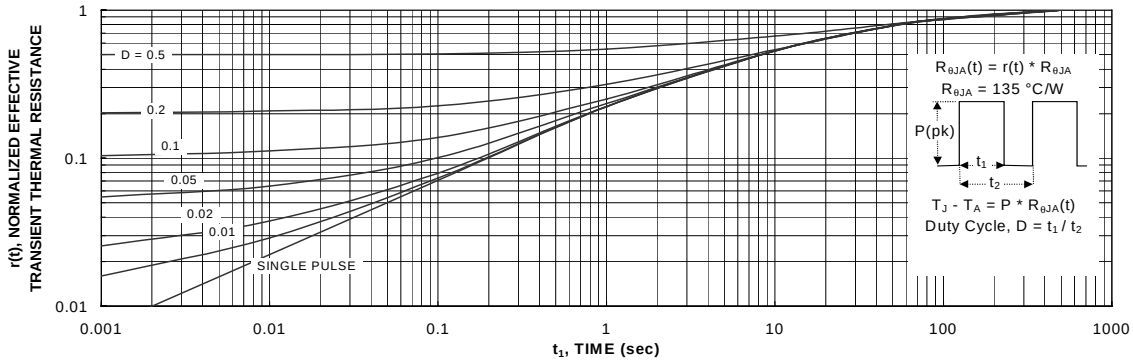


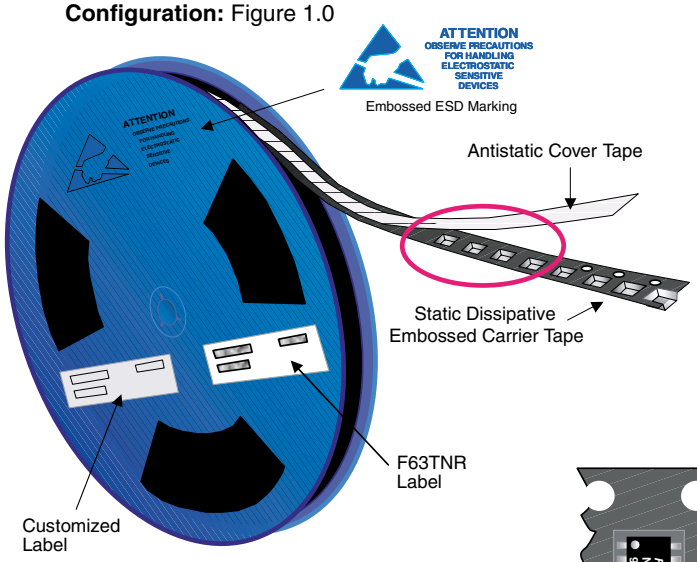
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

SOIC-8 Tape and Reel Data

FAIRCHILD SEMICONDUCTOR®

SOIC(8lds)Packaging Configuration: Figure 1.0

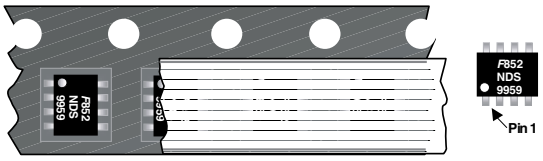


Packaging Description:

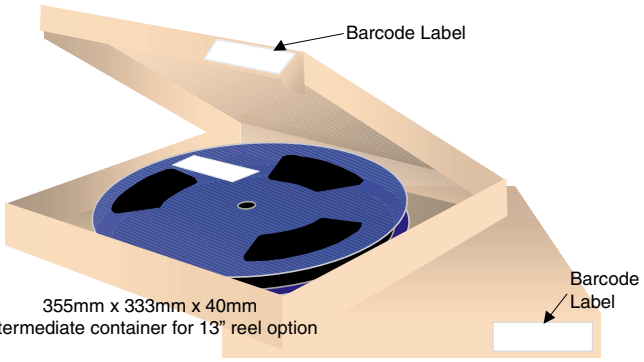
SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7" or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

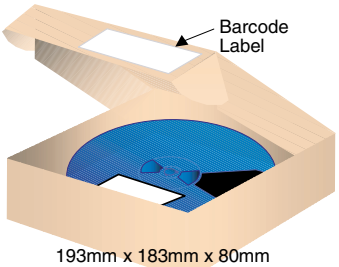
These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.

SOIC (8lds) Packaging Information				
Packaging Option	Standard (no flow code)	L86Z	F011	D84Z
Packaging type	TNR	Rail/Tube	TNR	TNR
Qty per Reel/Tube/Bag	2,500	95	4,000	500
Reel Size	13" Dia	-	13" Dia	7" Dia
Box Dimension (mm)	355x333x40	530x130x83	355x333x40	193x183x80
Max qty per Box	5,000	30,000	8,000	2,000
Weight per unit (gm)	0.0774	0.0774	0.0774	0.0774
Weight per Reel (kg)	0.6060	-	0.9696	0.1182
Note/Comments				



SOIC-8 Unit Orientation

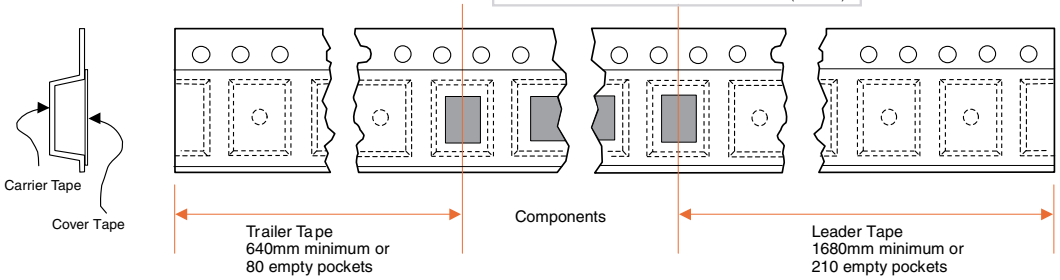




Barcode Label sample

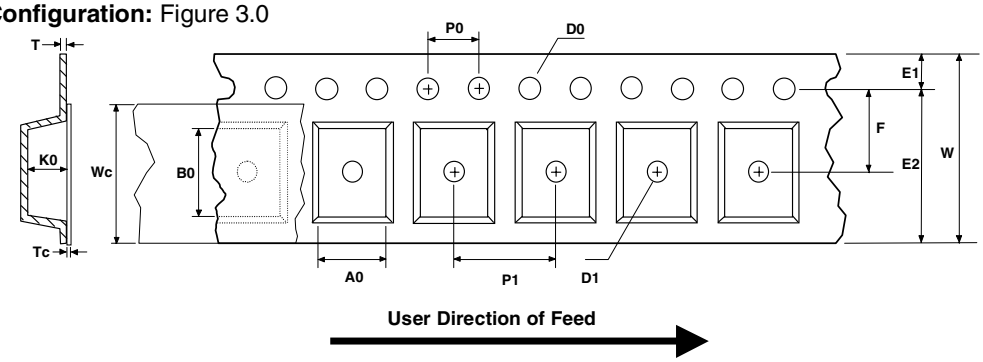
LOT: CBVK741B019 QTY: 2500
FSID: FDS9953A SPEC:
D/C1: Z9842AB QTY1: SPEC REV:
D/C2: QTY2: CPN:
FAIRCHILD SEMICONDUCTOR CORPORATION (F63T NR)

SOIC(8lds)Tape Leader and Trailer Configuration: Figure 2.0



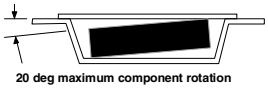
SOIC-8 Tape and Reel Data, continued

SOIC(8lds) Embossed Carrier Tape
Configuration: Figure 3.0

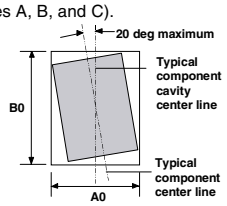


Dimensions are in millimeter														
Pkg type	**A0**	**B0**	**W**	**D0**	**D1**	**E1**	**E2**	**F**	**P1**	**P0**	**K0**	**T**	**Wc**	**Tc**
SOIC(8lds) (12mm)	5.30 +/-0.10	6.50 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

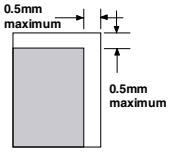
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

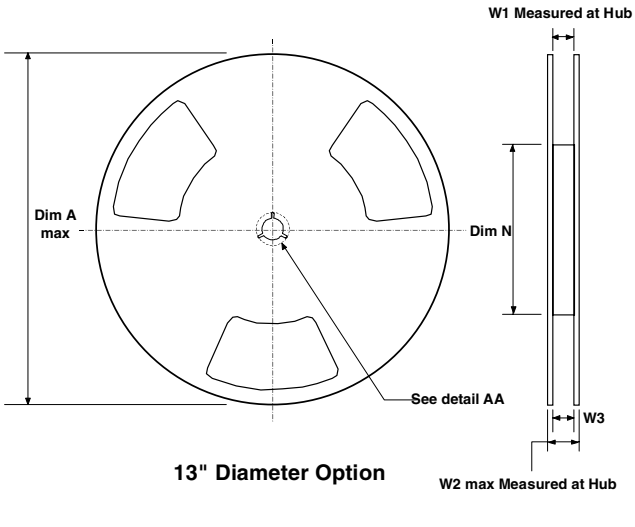


Sketch B (Top View)
Component Rotation

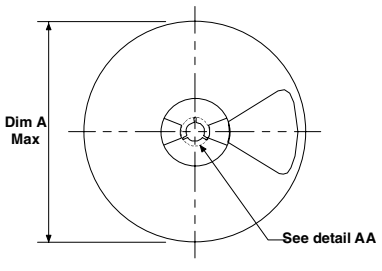


Sketch C (Top View)
Component lateral movement

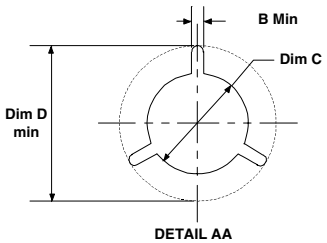
SOIC(8lds) Reel Configuration: Figure 4.0



13" Diameter Option



7" Diameter Option



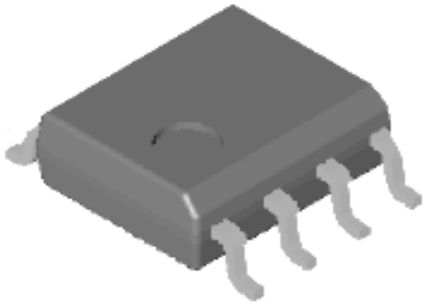
DETAIL AA

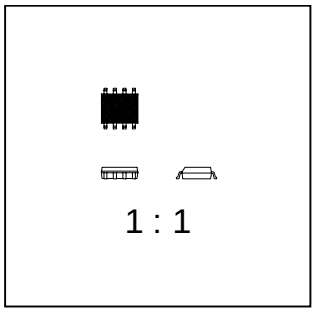
Dimensions are in inches and millimeters									
Tape Size	**Reel Option**	**Dim A**	**Dim B**	**Dim C**	**Dim D**	**Dim N**	**Dim W1**	**Dim W2**	**Dim W3 (LSL-USL)**
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 – 0.606 11.9 – 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 – 0.606 11.9 – 15.4

SOIC-8 Package Dimensions

FAIRCHILD SEMICONDUCTOR™

SOIC-8 (FS PKG Code S1)

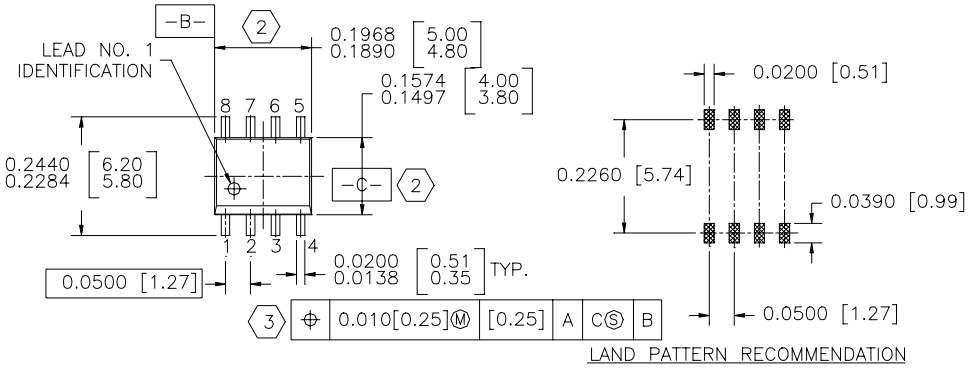


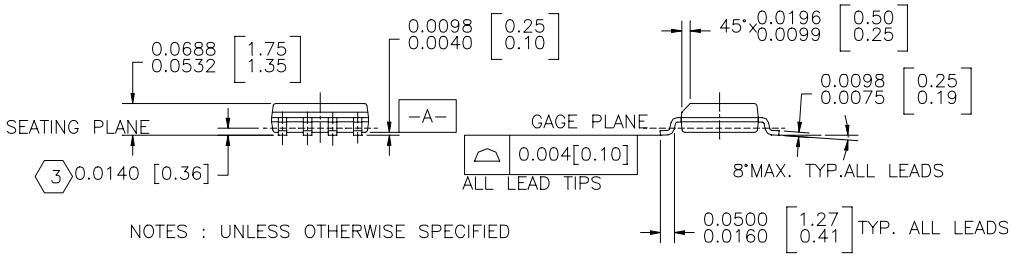


Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774





NOTES : UNLESS OTHERWISE SPECIFIED

1. STANDARD LEAD FINISH:
200 MICROINCHES / 5.08 MICRONS MINIMUM
LEAD / TIN (SOLDER) ON COPPER.

2. THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH

3. MAXIMUM LEAD 0.024 [0.609]

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DenseTrench™
DOME™
EcoSPARK™
E^2CMOS^{TM}
EnSigna™
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FACT Quiet Series™
FAST ®
FASTr™
FRFET™
GlobalOptoisolator™
GTO™
HiSeC™
ISOPLANAR™
LittleFET™
MicroFET™
MicroPak™
MICROWIRE™
OPTOLOGIC™
OPTOPLANAR™
PACMAN™
POP™
Power247™
PowerTrench®
QFET™
QS™
QT Optoelectronics™
Quiet Series™
SILENT SWITCHER®
SMART START™
STAR*POWER™
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SyncFET™
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FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.